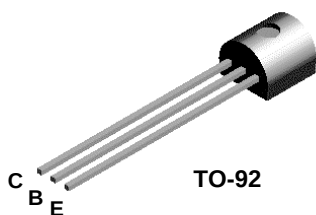
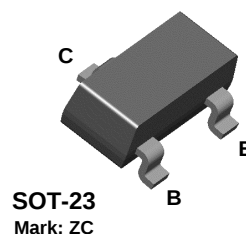


2N4124



MMBT4124



NPN General Purpose Amplifier

This device is designed as a general purpose amplifier and switch. The useful dynamic range extends to 100 mA as a switch and to 100 MHz as an amplifier.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	25	V
V_{CBO}	Collector-Base Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	200	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N4124	*MMBT4124	
P_D	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

NPN General Purpose Amplifier

(continued)

2N4124 / MMBT4124

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
--------	-----------	-----------------	-----	-----	-------

OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 1.0 \text{ mA}, I_B = 0$	25		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ } \mu\text{A}, I_E = 0$	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_C = 10 \text{ } \mu\text{A}, I_C = 0$	5.0		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 20 \text{ V}, I_E = 0$		50	nA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_C = 0$		50	nA

ON CHARACTERISTICS*

h_{FE}	DC Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 50 \text{ mA}, V_{CE} = 1.0 \text{ V}$	120 60	360	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.95	V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ $f = 100 \text{ MHz}$	300		MHz
C_{obo}	Output Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0,$ $f = 100 \text{ kHz}$		4.0	pF
C_{ibo}	Input Capacitance	$V_{BE} = 0.5 \text{ V}, I_C = 0,$ $f = 1.0 \text{ kHz}$		8.0	pF
C_{cb}	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0,$ $f = 100 \text{ kHz}$		4.0	pF
h_{fe}	Small-Signal Current Gain	$V_{CE} = 10 \text{ V}, I_C = 2.0 \text{ mA},$ $f = 1.0 \text{ kHz}$	120	480	
NF	Noise Figure	$I_C = 100 \text{ } \mu\text{A}, V_{CE} = 5.0 \text{ V},$ $R_S = 1.0 \text{ k}\Omega, f = 10 \text{ Hz to } 15.7 \text{ kHz}$		5.0	dB

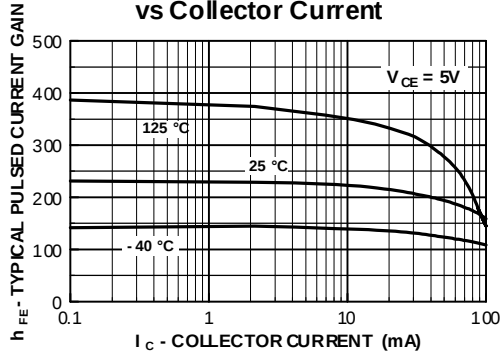
*Pulse Test: Pulse Width $\leq 300 \text{ } \mu\text{s}$, Duty Cycle $\leq 2.0\%$

NPN General Purpose Amplifier (continued)

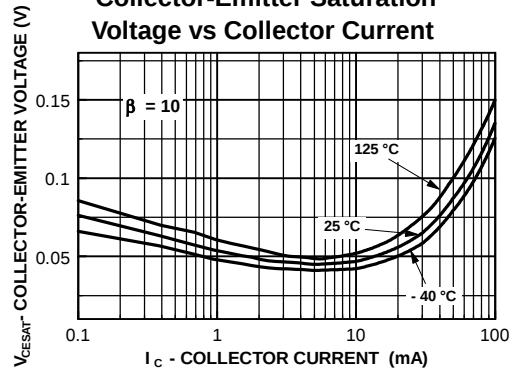
2N4124 / MMBT4124

Typical Characteristics

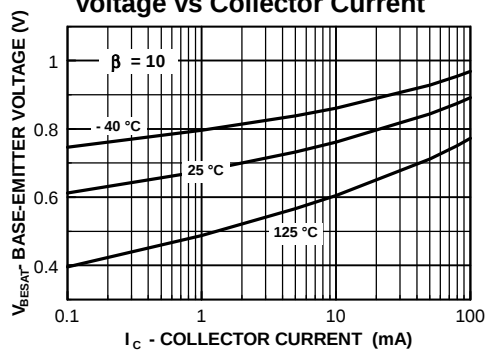
Typical Pulsed Current Gain
vs Collector Current



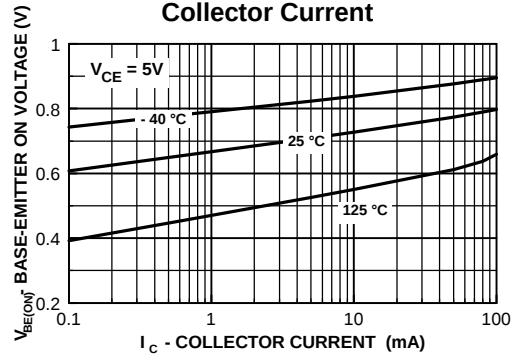
Collector-Emitter Saturation
Voltage vs Collector Current



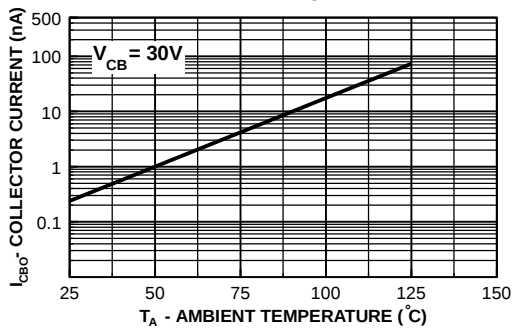
Base-Emitter Saturation
Voltage vs Collector Current



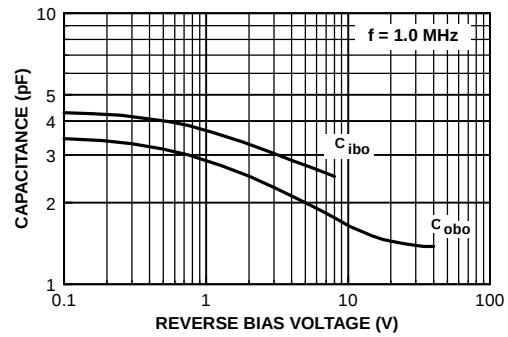
Base-Emitter ON Voltage vs
Collector Current



Collector-Cutoff Current
vs Ambient Temperature



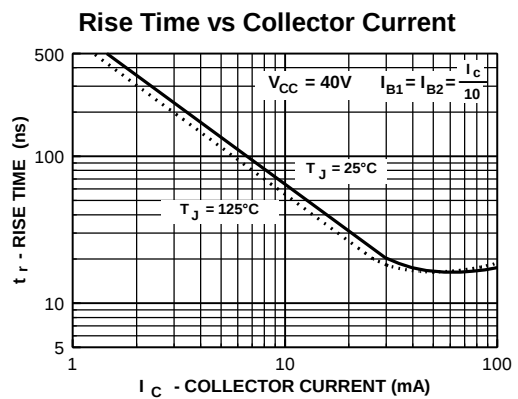
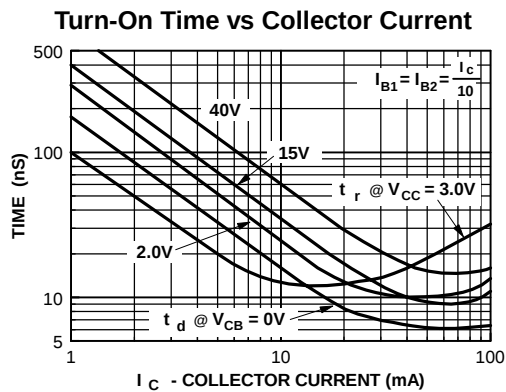
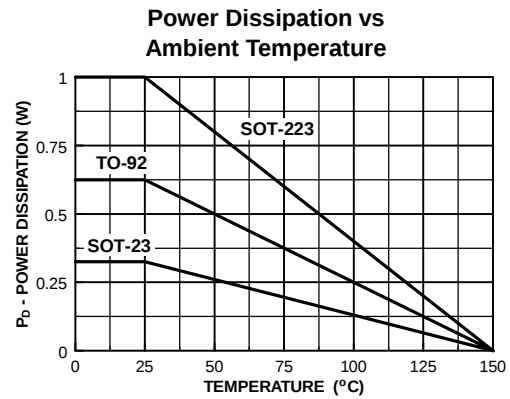
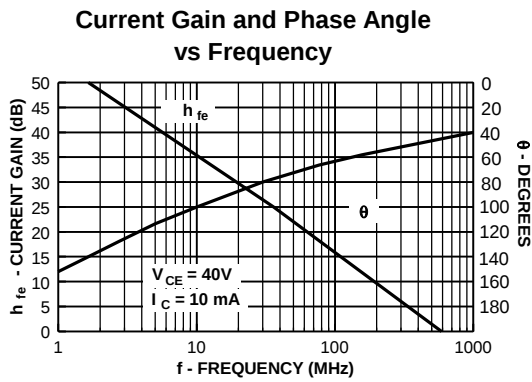
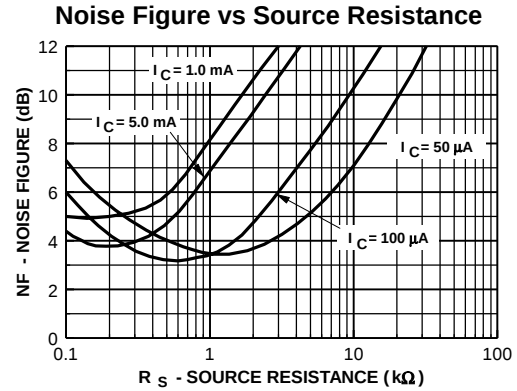
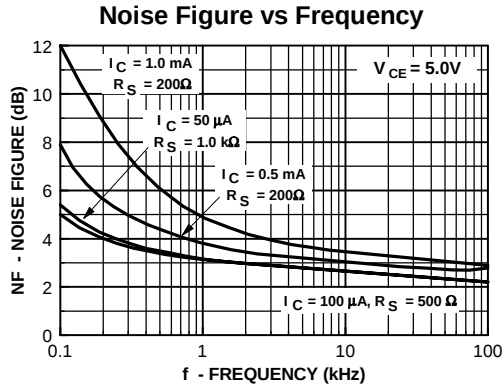
Capacitance vs
Reverse Bias Voltage



NPN General Purpose Amplifier

(continued)

Typical Characteristics (continued)

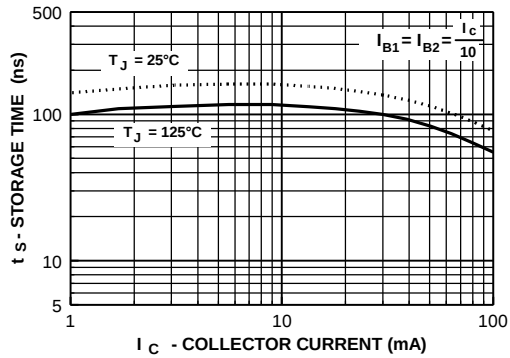


NPN General Purpose Amplifier (continued)

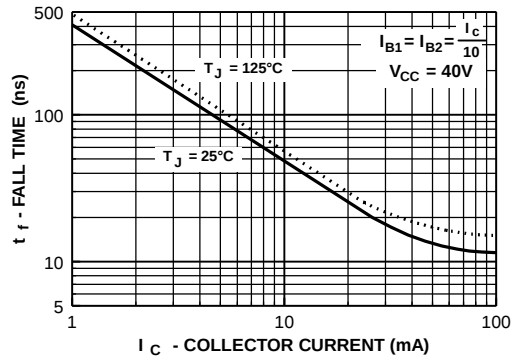
2N4124 / MMBT4124

Typical Characteristics (continued)

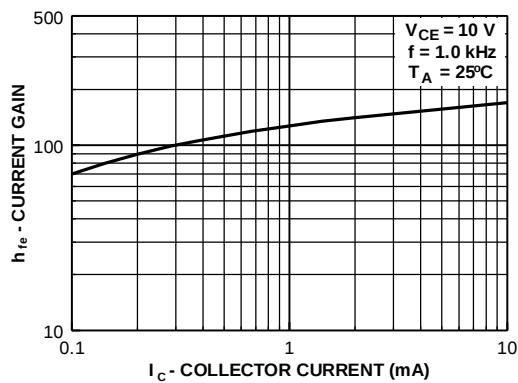
Storage Time vs Collector Current



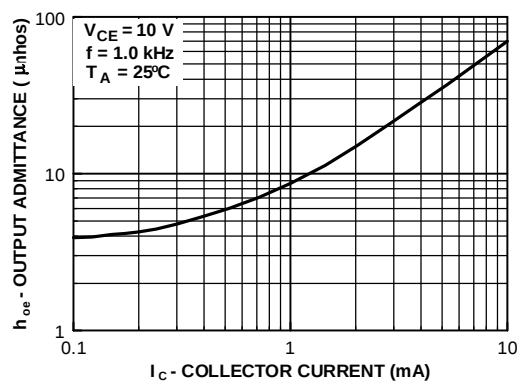
Fall Time vs Collector Current



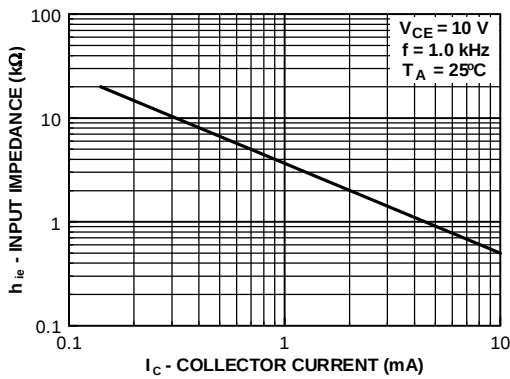
Current Gain



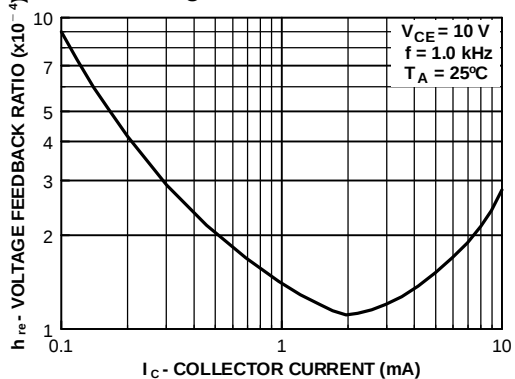
Output Admittance



Input Impedance



Voltage Feedback Ratio



Test Circuits

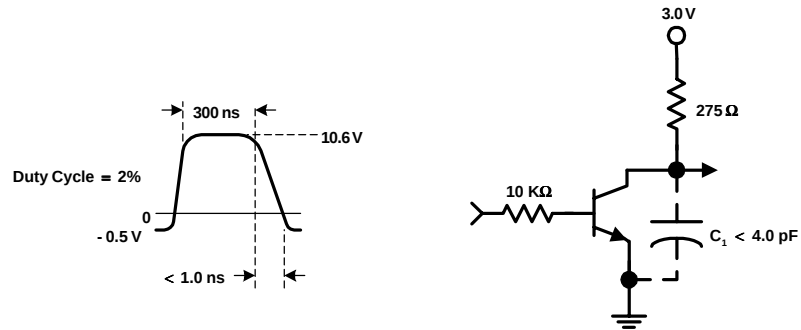


FIGURE 1: Delay and Rise Time Equivalent Test Circuit

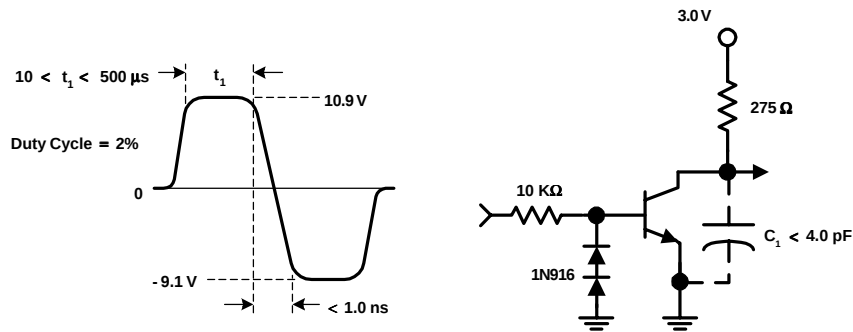


FIGURE 2: Storage and Fall Time Equivalent Test Circuit

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FASTr™	PowerTrench®	SyncFET™
Bottomless™	GlobalOptoisolator™	QFET™	TinyLogic™
CoolFET™	GTO™	QS™	UHC™
CROSSVOLT™	HiSeC™	QT Optoelectronics™	VCX™
DOME™	ISOPLANAR™	Quiet Series™	
E ² CMOS™	MICROWIRE™	SILENT SWITCHER®	
EnSigna™	OPTOLOGIC™	SMART START™	
FACT™	OPTOPLANAR™	SuperSOT™-3	
FACT Quiet Series™	PACMAN™	SuperSOT™-6	
FAST®	POP™	SuperSOT™-8	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.